Favorable consideration is earnestly solicited.

Respectfully submitted,

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Marked-up copy of the claims as amended:

3. (Amended) A semiconductor device [having over a substrate having an insulating surface a thin film transistor with a channel formation region formed of a semiconductor layer having an amorphous structure, a source region and a drain region each formed of a semiconductor layer containing one-conductive type impurity elements therein, a gate electrode formed between the semiconductor layer having the amorphous structure and the substrate, and an insulating layer formed on the gate electrode, the semiconductor device] comprising:

a substrate having an insulating surface;

a thin film transistor formed over the substrate, the thin-film transistor comprising a gate electrode formed over the substrate; and insulating layer formed on the gate electrode; a channel formation region formed in a semiconductor layer having an amorphous structure; source and drain regions, each of the source and drain regions comprising a semiconductor layer including one-conductive type impurity elements, formed over the semiconductor layer having the amorphous structure;

an interlayer insulating layer comprising an inorganic material and formed on the semiconductor layer having the amorphous structure and the semiconductor layer containing the one-conductive type impurity elements so as to be in contact with at least a part of the channel formation region;

a pixel electrode formed in contact with the insulating layer; and

an input terminal portion formed along an end portion of the substrate and electrically connected to a wiring of another substrate;

wherein the input terminal portion includes a first layer comprising the same material as that of the gate electrode and a second layer comprising the same material as that of the pixel electrode.